

Inherently selective plasma-assisted ALD: a feasibility study for III-nitride materials

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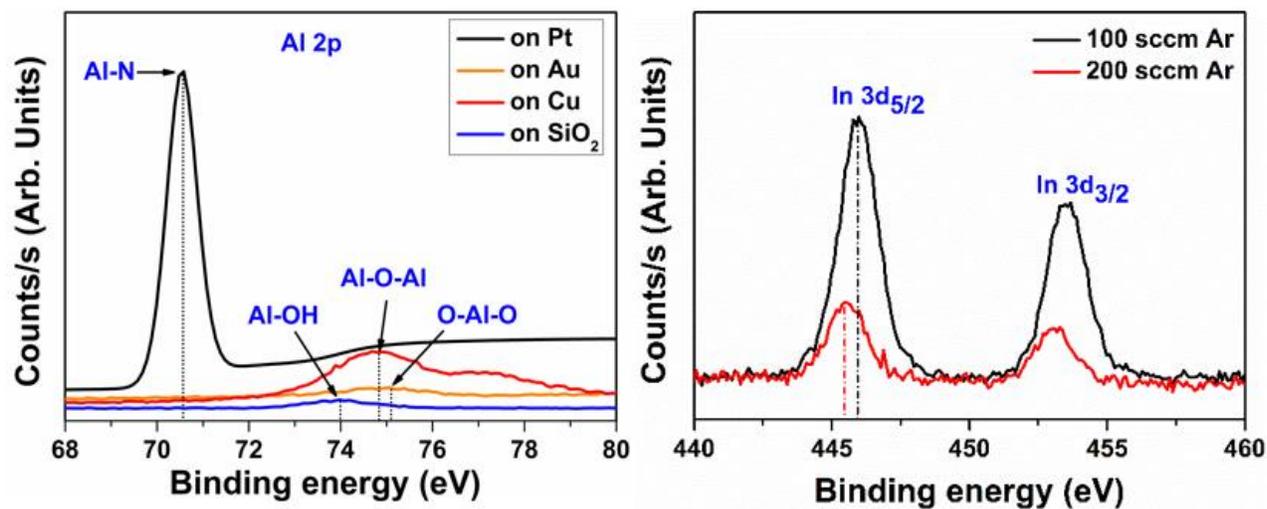


Figure 1. XPS analysis of PA-ALD grown AlN and InN films (a) XPS spectra of AlN films grown on various substrates, (b) The change in XPS spectra for InN samples as a function of Ar plasma gas flow rate, which influences the reactor pressure.